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	U	1	Document ID	Issue Date	Pages	Title
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6784081 B1	20040831	13	Gate structure forming method of fi effect transistor
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6772400 B2	200408031	25	Semi-phsysical modeling of HEMT high frequency small signal equivalent circuit models